



2:1 MIPI 4-Data Lane Switch

Features

- → 4-lane, 2:1 switches that support DHY
- → Data rate: 2.5 Gbps
- → Supports 2:1 clock differential signal
- → -3 dB Bandwidth: 4.5 GHz Typical
- → Low Crosstalk: -30 dB@1.25 GHz
- → Low Off Isolation: -26 dB@1.25 GHz
- → Input Signals 0 to 1.3V
- → RON: 6Ω Typical LP & HS MIPI
- → ΔR_{ON} : 0.1Ω Typical LP & HS MIPI
- → R_{ON_FLAT}: 0.3Ω Typical LP & HS MIPI
- → I_{CCZ}: 1µA Maximum
- → I_{CC}: 15µA Typical
- → C_{ON}: 1.5pF Typical
- → Skew of Opposite Transitions of the Same Output: 2ps Typical
- → V_{DD} Operating Range: 1.5V to 5V
- → ESD Tolerance: 2kV HBM
- → Packaging (Pb-free & Green): 36-Pin, CSP (GE) 2.44x2.44

Description

Diodes' PI3WVR646 is a four-data-lane MIPI-D-PHY switch. This 10 channel single-pole, double-throw (SPDT) switch is optimized for switching between two high-speed (HS) or low-power (LP) MIPI signal. The PI3WVR646 is designed for the MIPI specification and allows connection to a CSI or DSI module.

Applications

- → Cellular Phones, Smart Phone
- → Tablets
- → Laptops
- → Displays









Truth Table

SEL	OE Function	
LOW	LOW	CLK+ = CLKA+, CLK- = CLKA-, Dn(+/-) = DAn(+/-)
HIGH	LOW	CLK+ = CLKB+, CLK- = CLKB-, Dn(+/-) = DBn(+/-)
Х	HIGH	Clock and Data Ports High Impedance





Pin Description

Pin#	Pin Name	Signal Type	Description
A1	V _{CC}	Power	1.5V to 5V power supply
A2	GND	Ground	Ground
A3	DA4-	I/O	Negative differential signal 4 for port A
A4	DA4+	I/O	Positive differential signal 4 for port A
A5	ŌĒ	Ι	Output enable. if OE is low, IC is enabled. if OE is high, IC is power down and all I/Os are Hi-Z
A6	SEL	I/O	Switch logic control
B1	DB4-	I/O	Negative differential signal 4 for port B
B2	DB4+	I/O	Positive differential signal 4 for port B
B3	DA3-	I/O	Negative differential signal 3 for port A
B4	DA3+	I/O	Positive differential signal 3 for port A
B5	D4-	I/O	Negative differential signal 4 for COM port
B6	D4+	I/O	Positive differential signal 4 for COM port
C1	DB3-	I/O	Negative differential signal 3 for port B
C2	DB3+	I/O	Positive differential signal 3 for port B
C3	NC	-	Not Connect
C4	NC	-	Not Connect
C5	D3-	I/O	Negative differential signal 3 for COM port
C6	D3+	I/O	Positive differential signal 3 for COM port
D1	DB2-	I/O	Negative differential signal 2 for port B
D2	DB2+	I/O	Positive differential signal 2 for port B
D3	DA2-	I/O	Negative differential signal 2 for port A
D4	DA2+	I/O	Positive differential signal 2 for port A
D5	D2-	I/O	Negative differential signal 2 for COM port
D6	D2+	I/O	Positive differential signal 2 for COM port
E1	DB1-	I/O	Negative differential signal 1 for port B
E2	DB1+	I/O	Positive differential signal 1 for port B
E3	DA1-	I/O	Negative differential signal 1 for port A
E4	DA1+	I/O	Positive differential signal 1 for port A
E5	D1-	I/O	Negative differential signal 1 for COM port
E6	D1+	I/O	Positive differential signal 1 for COM port
F1	CLKB-	I/O	Clock negative differential signal for port B
F2	CLKB+	I/O	Clock positive differential signal for port B
F3	CLKA-	I/O	Clock negative differential signal for port A
F4	CLKA+	I/O	Clock positive differential signal for port A
F5	CLK-	I/O	Clock negative differential signal for COM port
F6	CLK+	I/O	Clock positive differential signal for COM port



Note:



PI3WVR646

Absolute Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

<u></u>	
V _{CC} , Supply Voltage,	0.5V to 6.0V
V _{CNTRL} , DC Input Voltage (OE, SEL) ⁽¹⁾	0.5V to V _{CC}
V _{SW} , DC Switch I/O Voltage ^(1,2)	0.3V to 4.0V
I _{IK} , DC Input Diodes Current	50mA
I _{OUT} , DC Output Current	25mA
T _{STG} , Storage Temperature	5° C to $+150^{\circ}$ C
Tj, Junction Temerature	125°C
ESD:	
Human Body Model, JEDEC: JESD22-A114, All Pins	2.0kV
Charged Device Model, JEDEC: JESD22-C101	1.0kV

Stresses greater than those listed under MAXIMUM RAT-INGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Note:

1. The input and output negative ratings may be exceeded if the input and output diode current ratings are observed.

2. V_{SW} refers to analog data switch paths.

Recommended Operating Conditions

The Recommended operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications.

Symbol	Description	Test Conditions	Min.	Max.	Units
V _{CC}	Supply Voltage		1.5	5.0	V
V _{CNTRL}	Control Input Voltage (SEL, \overline{OE}) ⁽¹⁾		0	V _{CC}	V
N	Switch I/O Voltage (CLK, D. CLKA, CLKB, DA, DB)	- HS Mode	0	0.5	V
V _{SW}	Switch I/O Voltage (CLK-, D-, CLKA-, CLKB-, DA-, DB-)	- LP Mode	0	1.3	V
T _A	Operating Temperature		-40	+85	°C

Note:

1. The control inputs must be held HIGH or LOW; they must not float.

DC and Transient Characteristics

All typical values are at $T_A = 25^{\circ}C$ unless otherwise specified.

				$T_{\rm A} = -40^{\rm o}{\rm C} \text{ to } +85^{\rm o}{\rm C}$			
Symbol	Description	Test Conditions	V _{CC} (V)	Min.	Тур.	Max.	Units
V _{IK}	Clamp Diode Voltage (OE, SEL)	$I_{IN} = -18mA$	1.5	-1.2		-0.6	V
V _{IH}	Input Voltage High	SEL, \overline{OE}	1.5 to 5	1.3			V
V _{IL}	Input Voltage Low	SEL, \overline{OE}	1.5 to 5			0.5	V
I _{IN}	Control Input Leakage (OE, SEL)	$V_{CNTRL} = 0$ to V_{CC}	5	-0.5		0.5	μΑ
I _{NO(OFF)} I _{NC(OFF)}	Off Leakage Current of Port CLKA-, DA-, CLKB- and DB-	$V_{SW} = 0.0 \le DATA \le 1.3V$	5	-0.5		0.5	μΑ
I _{A(ON)}	On Leakage Current of Common Ports (CLK-, D-)	$V_{SW} = 0.0 \le DATA \le 1.3V$	5	-0.5		0.5	μΑ





DC and Transient Characteristics Cont.

				$T_{\rm A} = -40^{\rm o}{\rm C}$ to $+85^{\rm o}{\rm C}$			
Symbol	Description	Test Conditions	V _{CC} (V)	Min.	Тур.	Max.	Units
I _{OFF}	Power-Off Leakage Current (All I/O Ports)	V _{SW} = 0.0 or 1.3V	0	-0.5		0.5	μΑ
I _{OZ}	Off-State Leakage	$\frac{V_{SW} = 0.0 \le DATA \le 1.3V,}{OE} = High$	5	-0.5		0.5	μΑ
			1.5				
R _{ON_MIPI_HS}	Switch On Resistance for HS MIPI	$I_{ON} = -8mA$, $OE = 0V$, SEL = V_{CC} or $0V$, CLKA,	2.5		6		Ω
NON_MIPI_H5		CLKB, DB- or DA- = $0.2V$	3.3				22
			5				
			1.5				
R _{ON_MIPI_LP}	Switch On Resistance for LP MIPI	$I_{ON} = -8mA, \overline{OE} = 0V,$ SEL = V _{CC} or 0V, CLKA,	2.5		6		Ω
		CLKB, DB- or DA- = $1.2V$	3.3				
			5				
	On Resistance Matching Between HS MIPI Channels ⁽¹⁾	$I_{ON} = -8mA$, $\overline{OE} = 0V$, SEL = V _{CC} or 0V, CLKA, CLKB, DB- or DA- = 0.2V	1.5		0.1		
$\Delta R_{ON_MIPI_HS}$			2.5				Ω
			3.3				
			5				
	On Resistance Matching Between LP MIPI Channels ⁽¹⁾	$I_{ON} = -8mA, \overline{OE} = 0V,$ SEL = V _{CC} or 0V, CLKA, CLKB, DB- or DA- = 1.2V	1.5		0.1		
$\Delta R_{ON_MIPI_LP}$			2.5				Ω
			5				
			1.5				
Dour profes		$I_{ON} = -8mA, \overline{OE} = 0V,$ SEL = V _{CC} or 0V, CLKA,	2.5		0.3		
R _{ON_FLAT_} MIPI_HS	On Resistance Flatness for HS MIPI	CLKB, DB- or DA- = 0 to	3.3				Ω
		0.3V	5				
			1.5				
R _{ON_FLAT_}		$I_{ON} = -8mA, \overline{OE} = 0V,$ SEL = V _{CC} or 0V, CLKA,	2.5		0.3		
MIPI_LP	On Resistance Flatness for LP MIPI	CLKB, DB- or DA- = 0 to	3.3				Ω
_		1.3V	5				
I _{CC}	Quiescent Supply Current	$\frac{V_{SEL} = 0 \text{ or } V_{CC}, I_{OUT} = 0,}{\overline{OE} = 0V}$	5		15	30	μΑ
I _{CCZ}	Quiescent Supply Current (High Impedance)	$\frac{V_{SEL} = 0 \text{ or } V_{CC}, I_{OUT} = 0,}{OE = 0V}$	5			1	μΑ
I _{CCT}	Increase in I_{CC} Current Per Control Voltage and V_{CC}	$V_{SEL} = 0 \text{ or } V_{CC}, \overline{OE} = 1.5V$	5		1		μΑ





AC Electrical Characteristics

All typical values are for $V_{CC} = 3.3V$ and $T_A = 25^{\circ}C$ unless otherwise specified.

				$T_A = -$	40°C to	+85°C	
Symbol	Description	Test Conditions	$V_{CC}(V)$	Min.	Тур.	Max.	Units
t _{INIT}	Initialization Time V _{CC} to Output ⁽¹⁾	$R_{L} = 50\Omega, C_{L} = 0pF, V_{SW}$ $= 0.6V$	1.5 to 5		60		μs
t _{EN}	Enable Time \overline{OE} to Output	$R_{L} = 50\Omega, C_{L} = 0pF, V_{SW}$ $= 0.6V$	1.5 to 5		60	150	μs
t _{DIS}	Disable Time \overline{OE} to Output	$R_{L} = 50\Omega, C_{L} = 0pF, V_{SW}$ $= 0.6V$	1.5 to 5		35	250	ns
t _{ON}	Turn-On Time SEL to Output	$\begin{aligned} R_{\rm L} &= 50\Omega, C_{\rm L} = 0 \text{pF}, V_{\rm SW} \\ &= 0.6 \text{V} \end{aligned}$	1.5 to 5		350	1100	ns
t _{OFF}	Turn-Off Time SEL to Output	$\begin{aligned} R_{L} &= 50\Omega, \ C_{L} = 0 p F, \ V_{SW} \\ &= 0.6 V \end{aligned}$	1.5 to 5		125	800	ns
t _{BBM}	Break-Before-Make Time	$\begin{aligned} R_L &= 50\Omega, \ C_L = 0 p F, \ V_{SW} \\ &= 0.6V \end{aligned}$	1.5 to 5			450	ns
t _{PD}	Propagation Delay ⁽¹⁾	$C_L = 0pF, R_L = 50\Omega$	1.5 to 5			0.25	ns
O _{IRR}	Off Isolation for MIPI ⁽¹⁾	$\label{eq:RL} \begin{split} \frac{R_L}{OE} &= 50\Omega, f = 1250 MHz, \\ \overline{OE} &= HIGH, V_{SW} = \\ 0.2 V_{PP} \end{split}$	1.5 to 5		-26		dB
X _{TALK}	Crosstalk for MIPI ⁽¹⁾	$\begin{split} R_L &= 50\Omega, f = 1250 \text{MHz}, \\ \text{SEL} &= \text{HIGH}, \text{V}_{\text{SW}} = \\ 0.2 \text{V}_{\text{PP}} \end{split}$	1.5 to 5			-30	dB
		$\label{eq:RL} \begin{array}{l} R_L = 50\Omega, f = 1250 MHz, \\ SEL = LOW, V_{SW} = 0.2 V_{PP} \end{array}$				-30	
T		$R_{L} = 50\Omega, C_{L} = 0pF,$ f = 1250MHz, V _{SW} = 0.2V _{PP}	1.5 to 5		-0.9		ID
I _{LOSS}	Insertion Loss ⁽¹⁾	$R_{L} = 50\Omega, C_{L} = 0pF,$ f = 750MHz, V _{SW} = 0.2V _{PP}	1.5 to 5		-0.7		dB
BW	-3db Bandwidth ⁽¹⁾	$\begin{aligned} R_{L} &= 50\Omega, \ C_{L} = 0 p F, \ V_{SW} \\ &= 0.2 V_{PP} \end{aligned}$	1.5 to 5	3.0	4.5		GHz

Note:

1. Guaranteed by characterization.





High-Speed-Related AC Electrical Characteristics

				$T_{A} = -4$	40°C to	+85°C	
Symbol	Description	Test Conditions	$V_{CC}(V)$	Min.	Тур.	Max.	Units
	HS Mode Skew of Opposite Transi- tions of the Same Output ⁽¹⁾	$R_{L} = 50\Omega, C_{L} = 0pF, V_{SW}$ $= 0.3V$	1.5 to 5		2	4	
t _{SK(P)}	HS Mode Slew of all group A or group B channels ⁽¹⁾	$R_{\rm L} = 50\Omega, C_{\rm L} = 0 \text{pF}, V_{\rm SW}$ $= 0.3 \text{V}$	1.5 to 5		4	7	ps

Note:

1. Guaranteed by characterization.

Capacitance

			$T_A = -$	40°C to	+85°C	
Symbol	Description	Test Conditions	Min.	Тур.	Max.	Units
C _{IN}	Control Pin Input Capacitance ⁽¹⁾	$V_{CC} = 0V, f = 1MHz$		2.1		pF
C _{ON}	On Capacitance ⁽¹⁾	$V_{CC} = 3.3V, \overline{OE} = 0V, f = 1250MHz$ (In HS common value)		1.5		pF
C _{OFF}	Off Capacitance ⁽¹⁾	V_{CC} or \overline{OE} = 3.3V, f = 1250MHz (Both sides in HS common value)		0.9		pF

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Note:

1. Guaranteed by characterization.







Fig 1. Crosstalk Setup



Fig 3. Differential Insertion Loss

Test Circuit for Dynamic Electrical Characteristics





Fig 2. Off-isolation setup





Test Circuit for Electrical Characteristics⁽¹⁻⁴⁾



Notes:

- 1. C_L = Load capacitance: includes jig and probe capacitance.
- 2. $R_{\rm T}$ = Termination resistance: should be equal to $Z_{\rm OUT}$ of the Pulse Generator
- 3. All input impulses are supplied by generators having the following characteristics: PRR \leq MHz, $Z_{O} = 50\Omega$, $t_{R} \leq 2.5ns$, $t_{F} \leq 2.5ns$.
- 4. The outputs are measured one at a time with one transition per measurement.

Switching Waveforms



Voltage Waveforms for Select Timing

Test Condition

Output 1 Test Condition	Output 2 Test Condition
PA = Low	PA = High
PB = High	PB = Low

Part Marking

CSP Package



Z: Die Rev YY: Year WW: Workweek 1st X: Assembly Site Code 2nd X: Fab Site Code





Packaging Mechanical: 36-CSP (GE)



For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

Ordering Information

Ordering Code	Package Code	Package Description
PI3WVR646GEEX	GE	36-Pin, 2.44x2.44, Wafer Level (CSP)

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See http://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. Thermal characteristics can be found on the company web site at www.diodes.com/design/support/packaging/

3. E = Pb-free and Green

4. X suffix = Tape/Reel





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